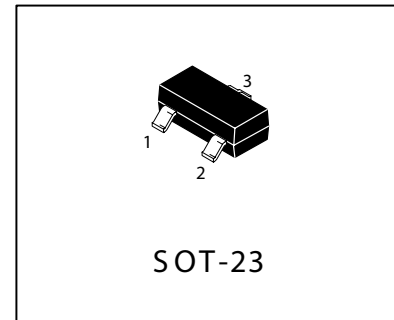
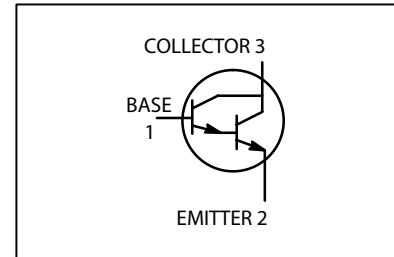


### NPN Transistors Darlington Amplifier

 Lead(Pb)-Free



#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector- Emitter Voltage	$V_{CES}$	30	Vdc
Collector- Base Voltage	$V_{CBO}$	30	Vdc
Emitter- Base Voltage	$V_{EBO}$	10	Vdc
Collector Current - Continuous	$I_C$	300	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR $\pm 5$ Board <sup>(1)</sup> $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, <sup>(2)</sup> $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	- 55 to +150	$^\circ\text{C}$

#### DEVICE MARKING

MMBTA13 = 1M; MMBTA14LT1 = 1N

#### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

#### OFF CHARACTERISTICS

Collector- Emitter Breakdown Voltage ( $I_C = 100 \mu\text{Adc}$ , $V_{BE} = 0$ )	$V_{(BR)CES}$	30	-	Vdc
Collector Cutoff Current ( $V_{CB} = 30 \text{Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	100	nAdc
Emitter Cutoff Current ( $V_{EB} = 10 \text{Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	100	nAdc

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS (3)</b>				
DC Current Gain ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	MMBTA13	5000	-	-
	MMBTA14	10,000	-	-
( $I_C = 100\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	MMBTA13	10,000	-	-
	MMBTA14	20,000	-	-
Collector- Emitter Saturation Voltage ( $I_C = 100\text{ mAdc}$ , $I_B = 0.1\text{ mAdc}$ )	$V_{CE(sat)}$	-	1.5	Vdc
Base- Emitter On Voltage ( $I_C = 100\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$V_{BE}$	-	2.0	Vdc

**SMALL- SIGNAL CHARACTERISTICS**

Current- Gain - Bandwidth Product (4) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	125	-	MHz
--	-------	-----	---	-----

- Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .
- $f_T = |h_{fe}| \cdot f_{test}$

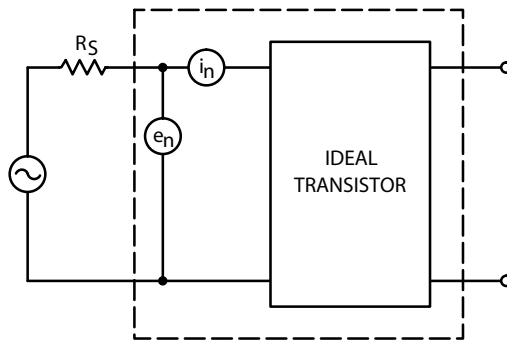


FIG.1. Transistor Noise Model

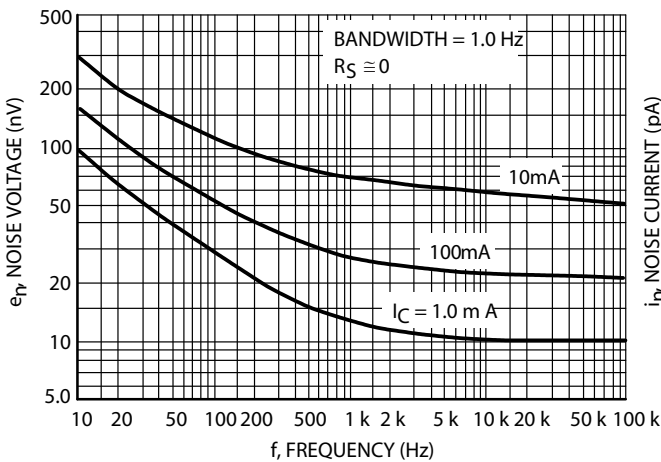


FIG.2 Noise Voltage

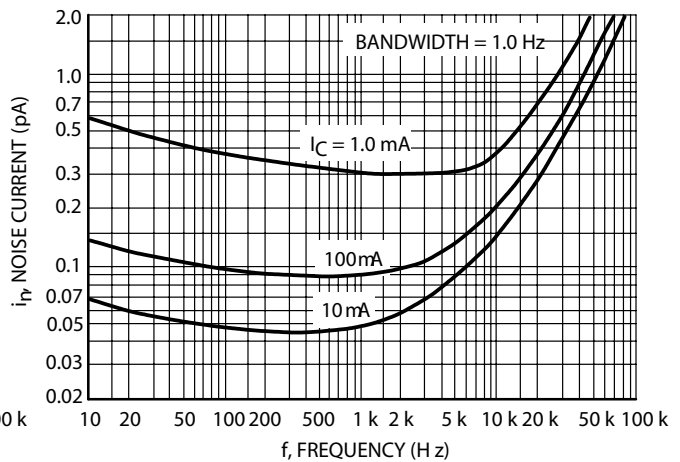


FIG.3 Noise Current

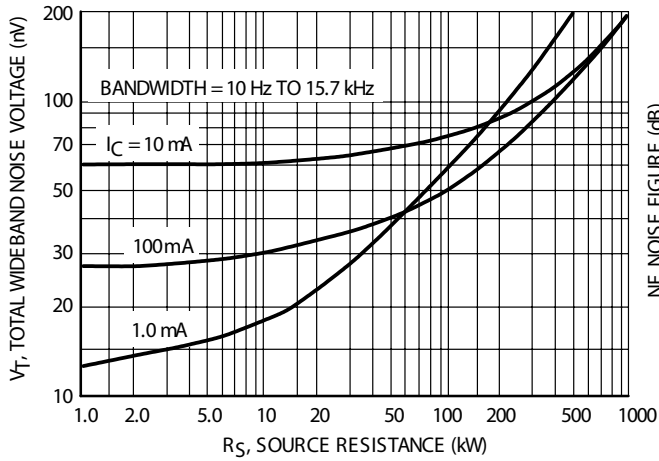


FIG.4 Total Wideband Noise Voltage

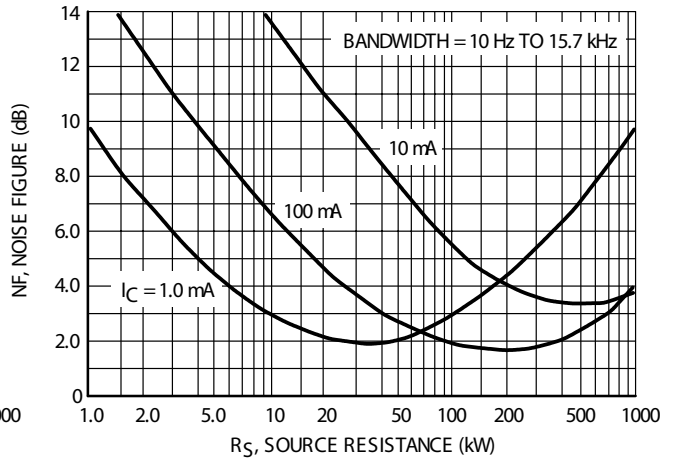


FIG.5 Wideband Noise Figure

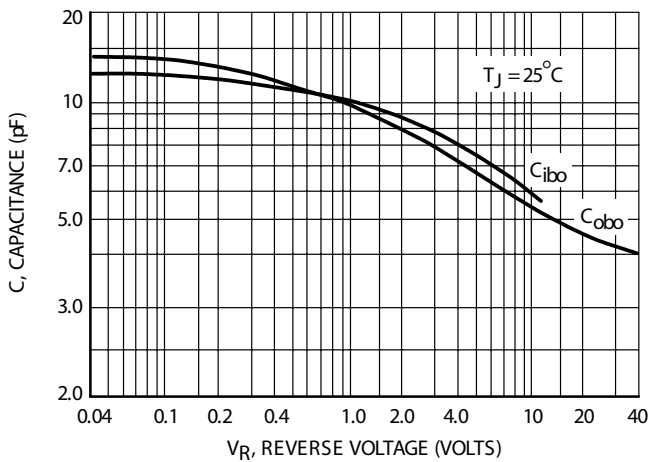


FIG.6 Capacitance

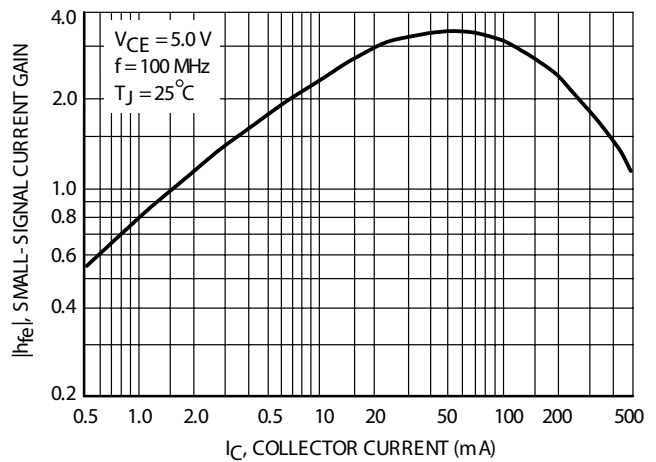


FIG.7 High Frequency Current Gain

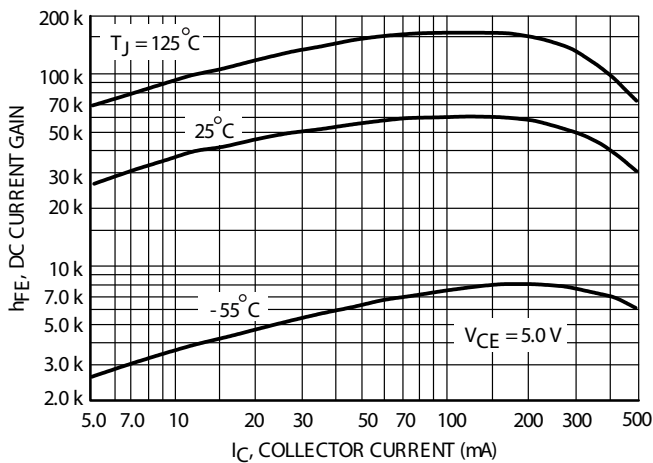


FIG.8 DC Current Gain

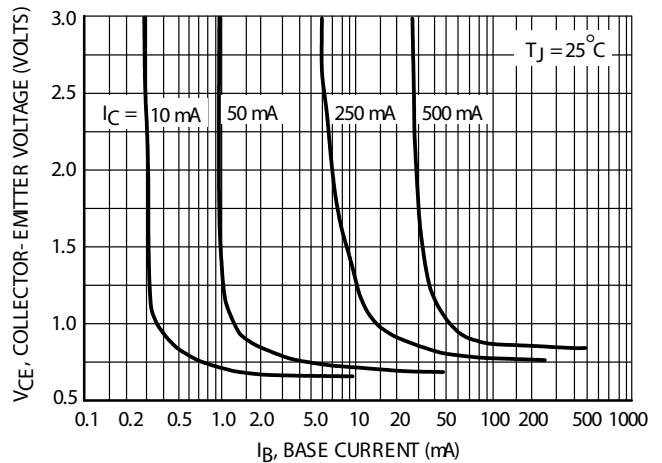
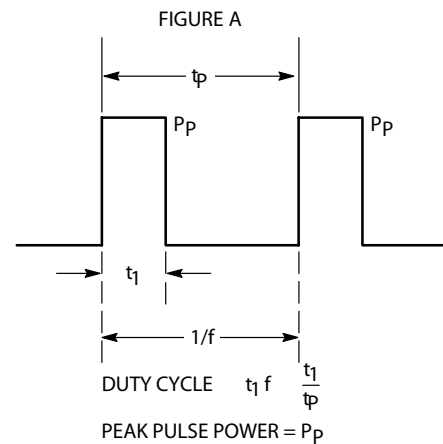
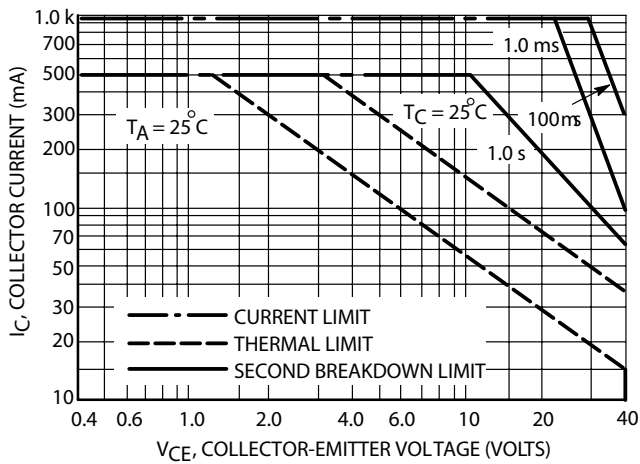
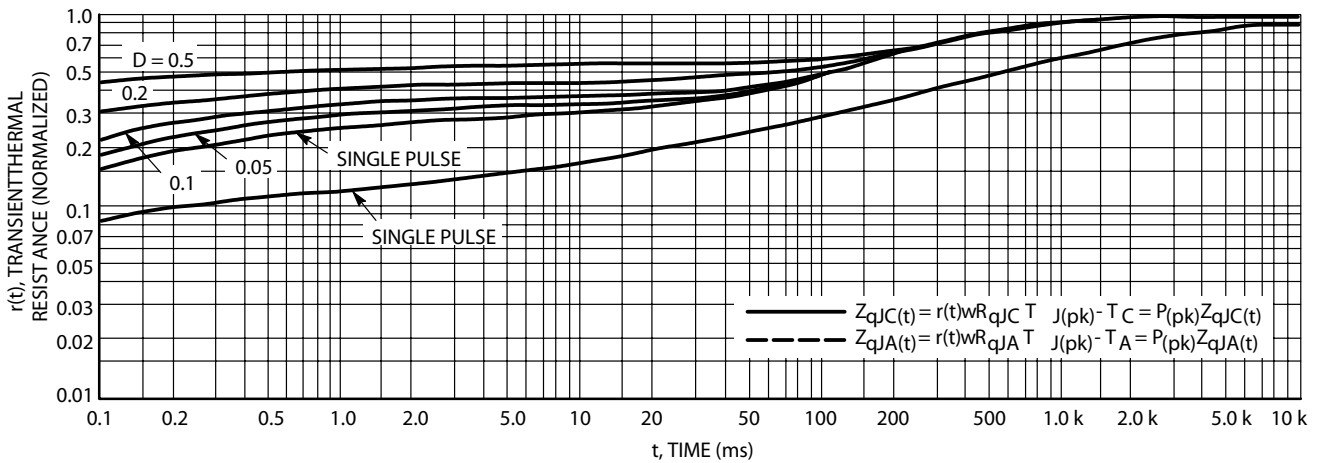
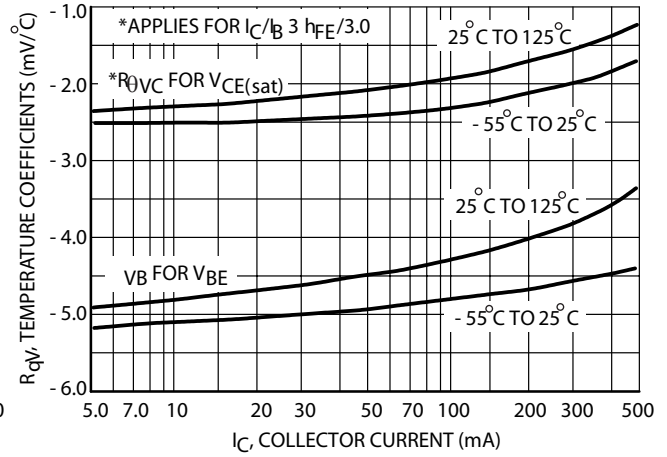
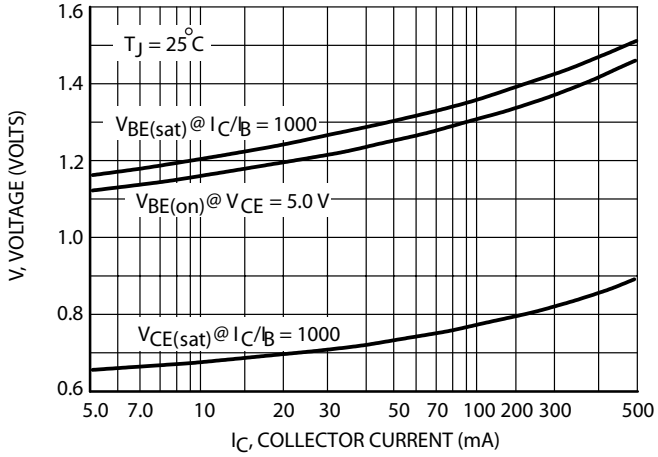


FIG.9 Collector Saturation Region

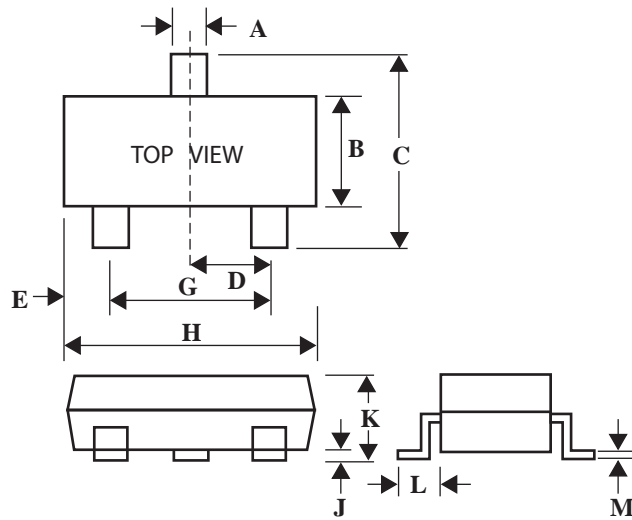
# MMBTA13 MMBTA14



Design Note: Use of Transient Thermal Resistance Data

**SOT-23 Package Outline Dimensions**

Unit:mm



Dim	Min	Max
A	0.35	0.51
B	1.19	1.80
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.60
L	0.30	0.61
M	0.076	0.25